ABSTRACT OF THE DISCLOSURE

3-5 GROUP COMPOUND SEMICONDUCTOR AND LIGHT EMITTING DEVICE

Provide is a 3-5 group compound semiconductor having a concentration of a p-type dopant of 1×10^{17} cm^{-3} or more and 1×10^{21} cm^{-3} or less, which can be laminated to control the carrier concentration of an InGaAlN-type mixed crystal in a low range with high reproducibility. Also provided is a 3-5 group compound semiconductor in which the carrier concentration of an InGaAlN-type mixed crystal is controlled in a low range with high reproducibility, and a light emitting device having high light emitting efficiency.